GSM1382XF

100V N-Channel MOSFET

Product Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

The device is well suited for high efficiency fast switching applications.

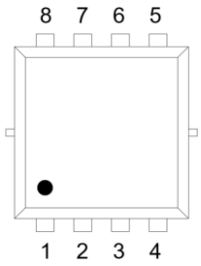
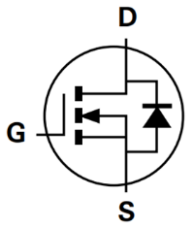
Features

- $R_{DS(ON)}$ = 7.6mΩ @ V_{GS}=10V
- $R_{DS(ON)}$ = 10.8mΩ @ V_{GS}=4.5V
- DFN5X6-8L Package
- RoHS Compliant and Halogen Free

Applications

- MB / VGA / Vcore
- POL Applications
- SMPS

Packages & Pin Assignments

DFN5X6-8L	Equivalent Circuit
	

Pin	Symbol	Description	Pin	Symbol	Description
1	S	Source	8	D	Drain
2	S	Source	7	D	Drain
3	S	Source	6	D	Drain
4	G	Gate	5	D	Drain

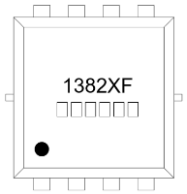
Ordering and Marking Information

Ordering Information			
Part Number	**Package**	**Part Marking**	**Quantity / Reel**
GSM1382XF	DFN5X6-8L	1382XF □□□□□□	3,000 PCS

GSM1382 1 2

- **Product Code:** GSM1382
- **Package Code:** 1 is **X** for DFN5X6-8L
- **Green Level:** 2 is **F** for RoHS Compliant and Halogen Free

Marking Information



- **Product Code:** 1382XF
- **GS Code:** □□□□□□
- The dot • indicates Pin1

Absolute Maximum Ratings (T_C= 25ºC unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C=25ºC	76	A
		T_C=100ºC	47	
I_{DM}	Pulsed Drain Current [1]		200	A
I_{AS}	Single Pulse Avalanche Current, L = 0.1mH [1]		25	A
E_{AS}	Single Pulse Avalanche Energy, L = 0.1mH [1]		62.5	mJ
P_D	Power Dissipation	T_C=25ºC	89	W
		T_C=100ºC	35	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		1.4	ºC/W
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient [2]		62	ºC/W
T_J	Operating Junction Temperature Range		-55 to +150	ºC
T_{STG}	Storage Temperature Range		-55 to +150	ºC

NOTE:
1. Single pulse width is limited by max junction temperature.
2. The device mounted on 1in^2 FR4 PCB with 2oz. Coppe

Electrical Characteristics (T_J = 25ºC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	100	-	-	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V, V_{GS}=0V	-	-	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.2	-	2.5	V
$R_{DS(ON)}$	Drain-Source On-Resistance	V_{GS}=10V, I_D=20A	-	6.4	7.6	mΩ
		V_{GS}=4.5V, I_D=10A	-	8.4	10.8	
gfs	Forward Transconductance	V_{DS}=5V, I_D=20A	-	30	-	S
Dynamic Characteristics						
R_g	Gate Resistance	f=1MHz		1		Ω
C_{iss}	Input Capacitance	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	2180	2980	pF
C_{oss}	Output Capacitance		-	550	-	
C_{rss}	Reverse Transfer Capacitance		-	13	-	
Q_g	Total Gate Charge	V_{DS}=50V, I_D=10A V_{GS}=10V	-	39	58	nC
Q_{gs}	Gate-Source Charge		-	4.4	-	
Q_{gd}	Gate-Drain Charge		-	12	-	
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=50V, I_D=10A V_{GS}=10V, Rg=6Ω	-	14	-	ns
t_r	Turn-On Rise Time		-	21	-	
$t_{d(off)}$	Turn-Off Delay Time		-	34	-	
t_f	Turn-Off Fall Time		-	24	-	
Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_S=1A	-	-	1	V
t_{rr}	Reverse Recovery Time	V_R=50V, I_F=10A , dI/dt=100A/μs	-	67	-	ns
Q_{rr}	Reverse Recovery Charge		-	153	-	nC

Typical Performance Characteristics

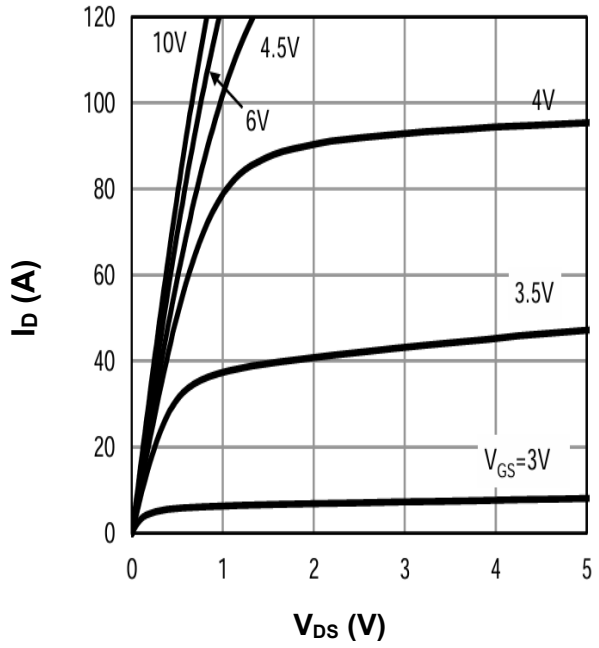


FIG.1 Output Characteristics

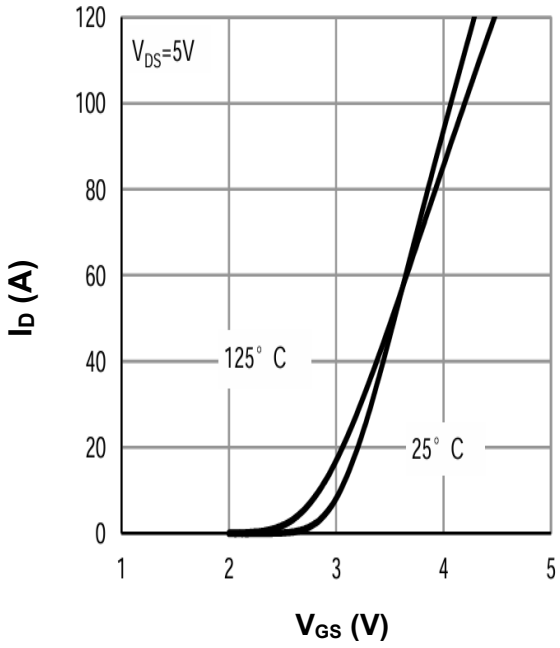


FIG.2 Transfer Characteristics

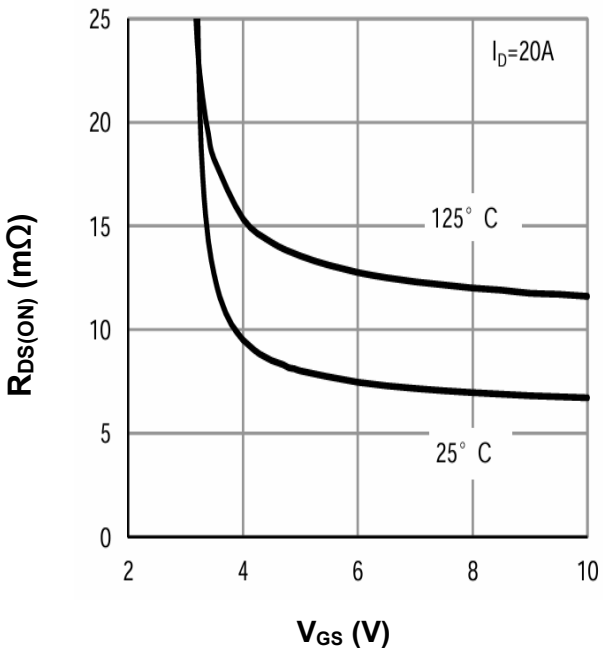


FIG.3 On-Resistance vs. Gate Voltage

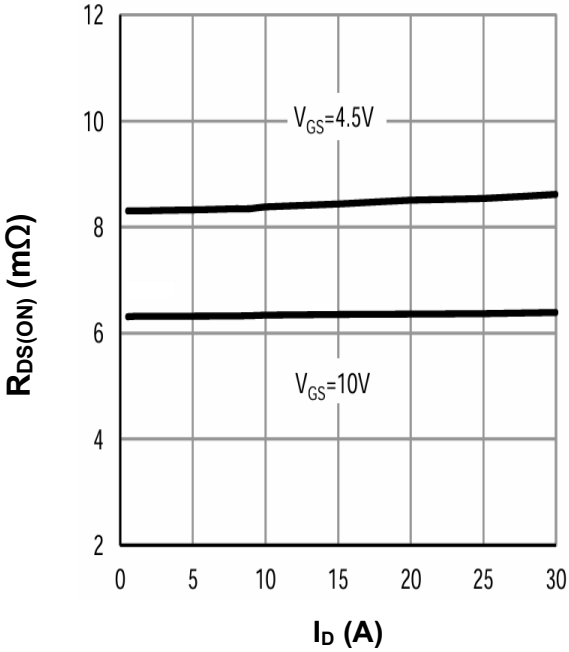


FIG.4 On-Resistance vs. Drain Current

Typical Performance Characteristics

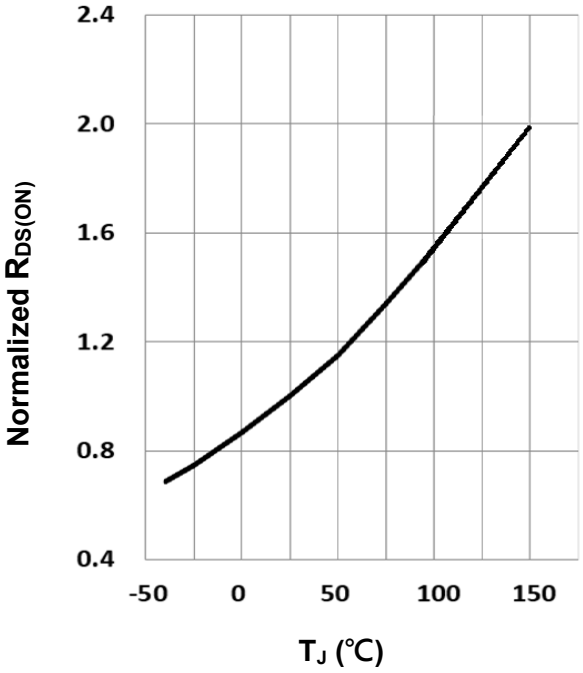


FIG.5 Normalized On-Resistance vs. T_J

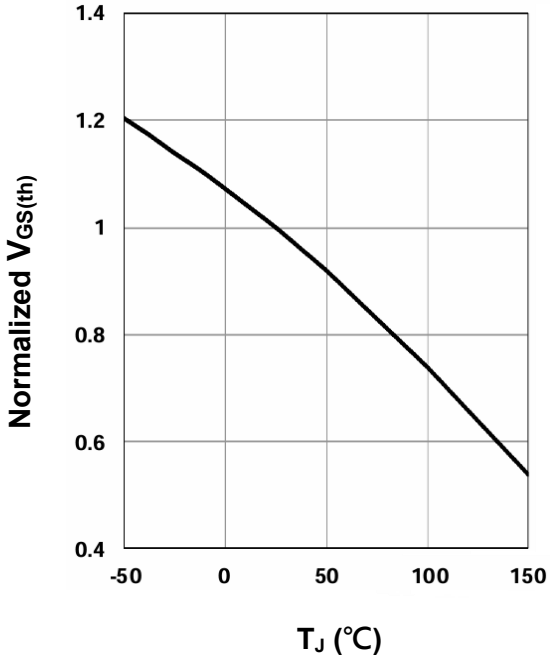


FIG.6 Normalized $V_{GS(th)}$ vs. T_J

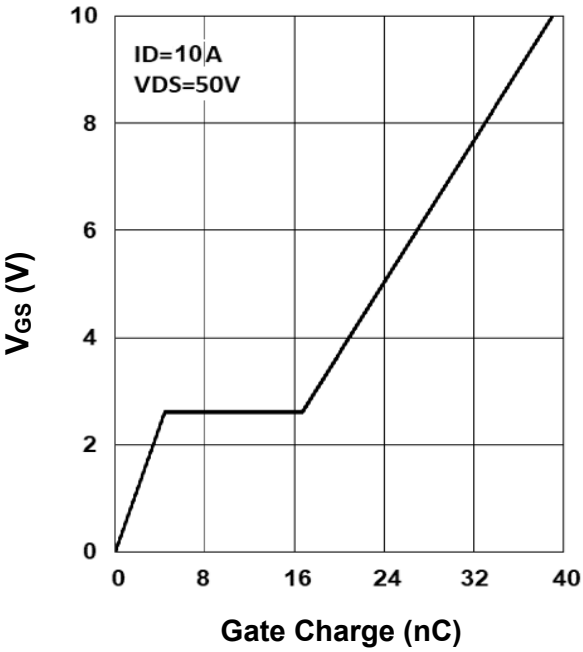


FIG.7 Gate Charge Characteristics

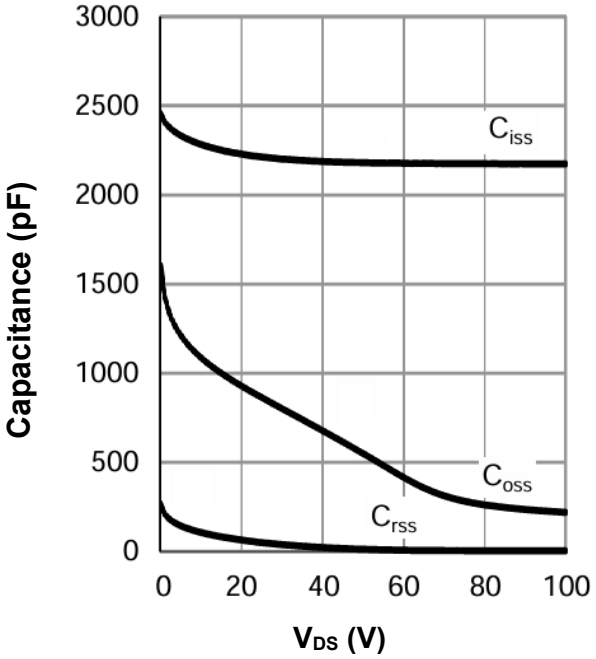


FIG.8 Capacitance Characteristics

Typical Performance Characteristics

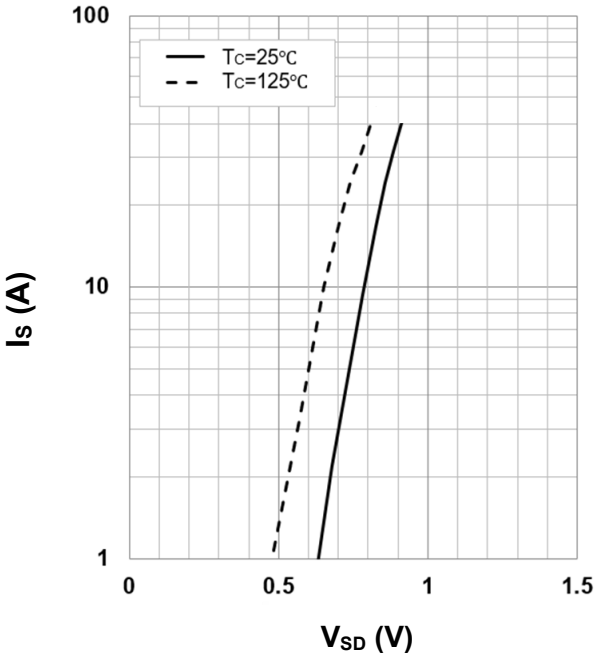


FIG.9 Diode Characteristics

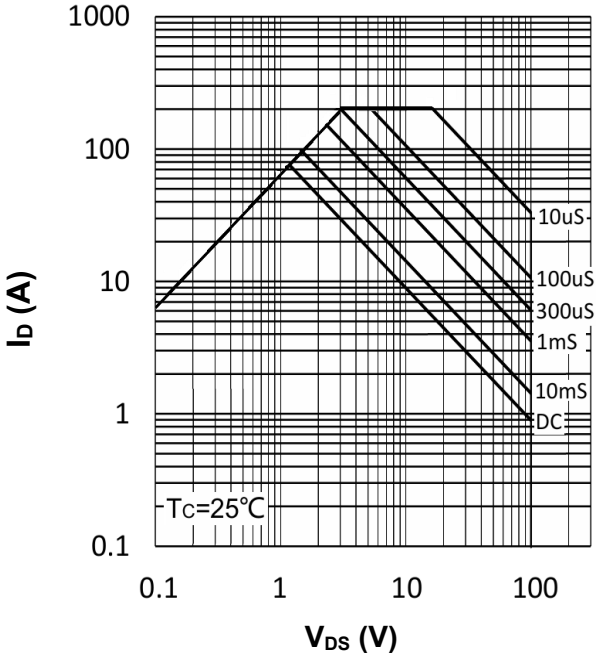


FIG.10 Maximum Safe Operation Area

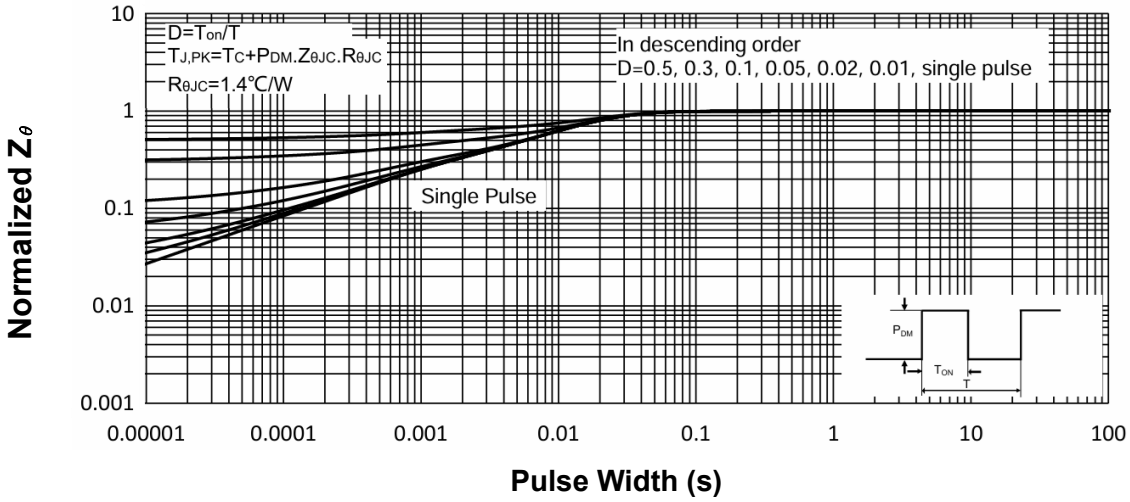
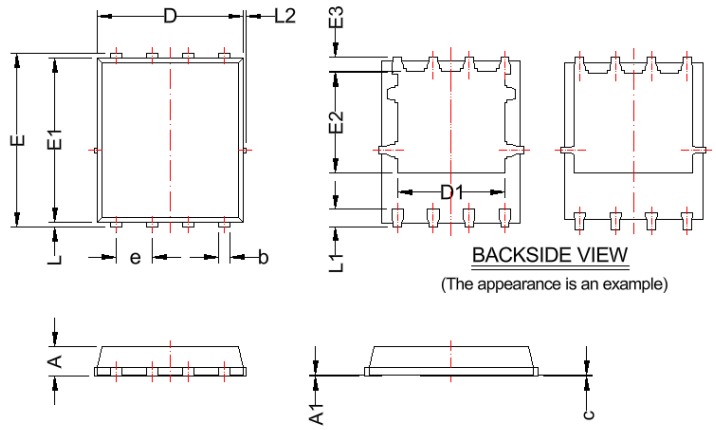


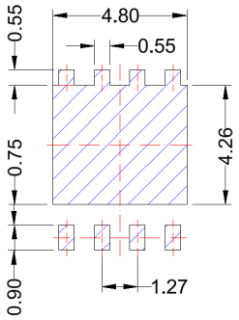
FIG.11 Normalized Transient Impedance

DFN5X6-8L

Package Dimension



Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.25	0.51	0.010	0.020
c	0.20	0.35	0.008	0.014
D	4.80	5.40	0.189	0.213
D1	3.40	4.60	0.134	0.181
E	5.90	6.20	0.232	0.244
E1	5.40	5.90	0.213	0.232
E2	3.20	3.80	0.126	0.150
E3	0.40	0.80	0.016	0.031
e	1.27 BSC		0.050 BSC	
L	0.06	0.25	0.002	0.010
L1	0.34	0.75	0.013	0.030
L2	---	0.15	---	0.006

NOTE:

1. Dimensions are exclusive of Burrs, Mold Flash and Tie Bar extrusions.

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